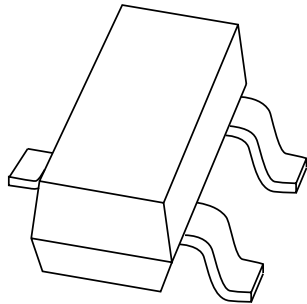


# DATA SHEET



## **MMBT3906** PNP switching transistor

Product data sheet  
Supersedes data of 2000 Apr 11

2003 Mar 18

# PNP switching transistor

# MMBT3906

### FEATURES

- Collector current capability  $I_C = -200$  mA
- Collector-emitter voltage  $V_{CEO} = -40$  V.

### APPLICATIONS

- General switching and amplification.

### DESCRIPTION

PNP switching transistor in a SOT23 plastic package.  
NPN complement: MMBT3904.

### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
MMBT3906	7B*

#### Note

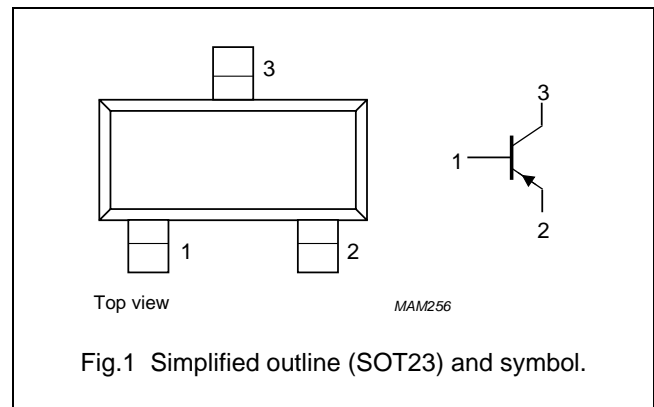
- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	-40	V
$I_C$	collector current (DC)	-200	mA

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	-	-40	V
$V_{CEO}$	collector-emitter voltage	open base	-	-40	V
$V_{EBO}$	emitter-base voltage	open collector	-	-6	V
$I_C$	collector current (DC)		-	-200	mA
$I_{CM}$	peak collector current		-	-200	mA
$I_{BM}$	peak base current		-	-100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C; note 1	-	250	mW
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	junction temperature		-	150	°C
$T_{amb}$	operating ambient temperature		-65	+150	°C

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

## PNP switching transistor

## MMBT3906

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

## Note

1. Transistor mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

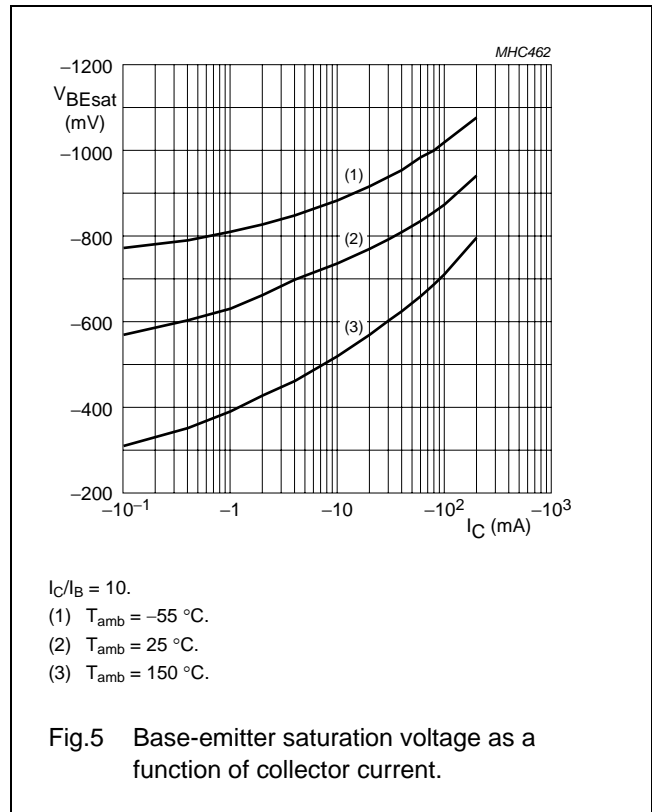
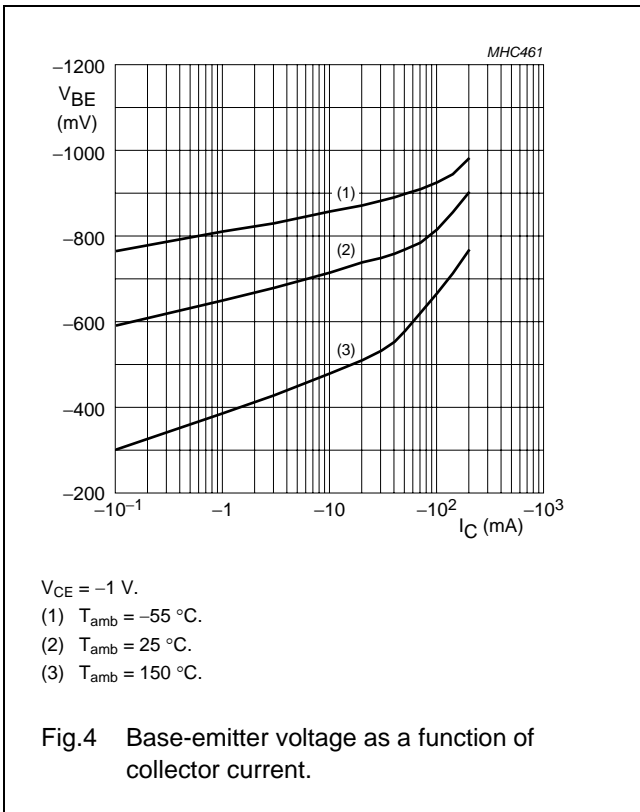
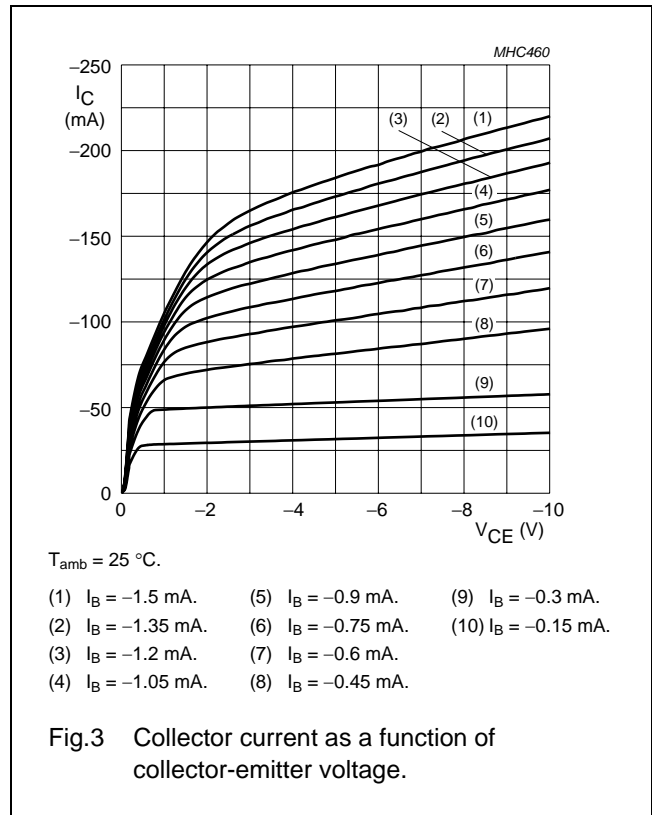
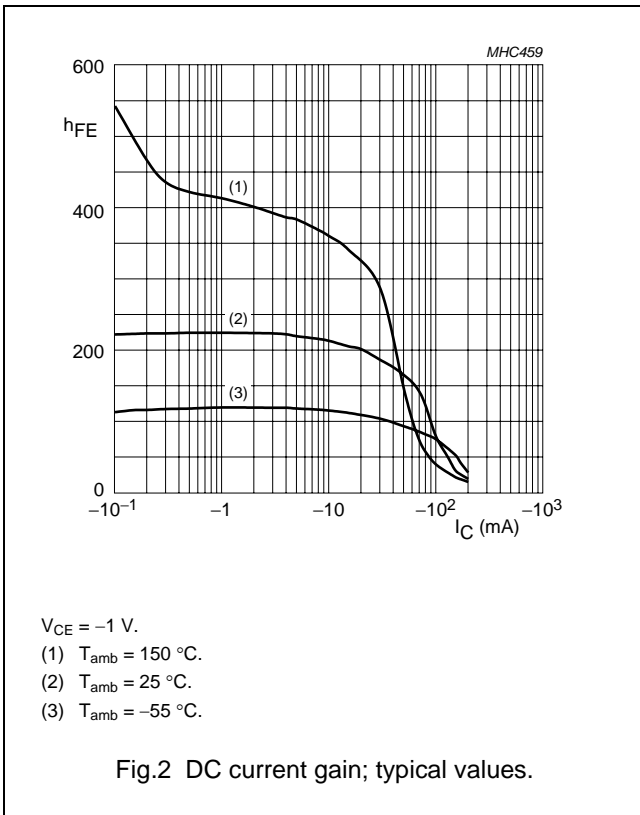
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	–	–50	nA
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = -6\text{ V}$	–	–50	nA
$h_{FE}$	DC current gain	$V_{CE} = -1\text{ V}$ ; see Fig.2 $I_C = -0.1\text{ mA}$ $I_C = -1\text{ mA}$ $I_C = -10\text{ mA}$ $I_C = -50\text{ mA}$ $I_C = -100\text{ mA}$	60 80 100 60 30	– – 300 – –	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$	–	–250	mV
		$I_C = -50\text{ mA}; I_B = -5\text{ mA}$	–	–400	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$	–	–850	mV
		$I_C = -50\text{ mA}; I_B = -5\text{ mA}$	–	–950	mV
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = -5\text{ V}; f = 1\text{ MHz}$	–	4.5	pF
$C_e$	emitter capacitance	$I_C = i_c = 0; V_{EB} = -500\text{ mV}; f = 1\text{ MHz}$	–	10	pF
$f_T$	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -20\text{ V}; f = 100\text{ MHz}$	250	–	MHz
F	noise figure	$I_C = -100\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 1\text{ k}\Omega; f = 10\text{ Hz to }15.7\text{ kHz}$	–	4	dB

## Switching times (between 10% and 90% levels); see Fig.7

$t_d$	delay time	$I_{Con} = -10\text{ mA}; I_{Bon} = -1\text{ mA}; I_{Boff} = 1\text{ mA}$	–	35	ns
$t_r$	rise time		–	35	ns
$t_s$	storage time		–	225	ns
$t_f$	fall time		–	75	ns

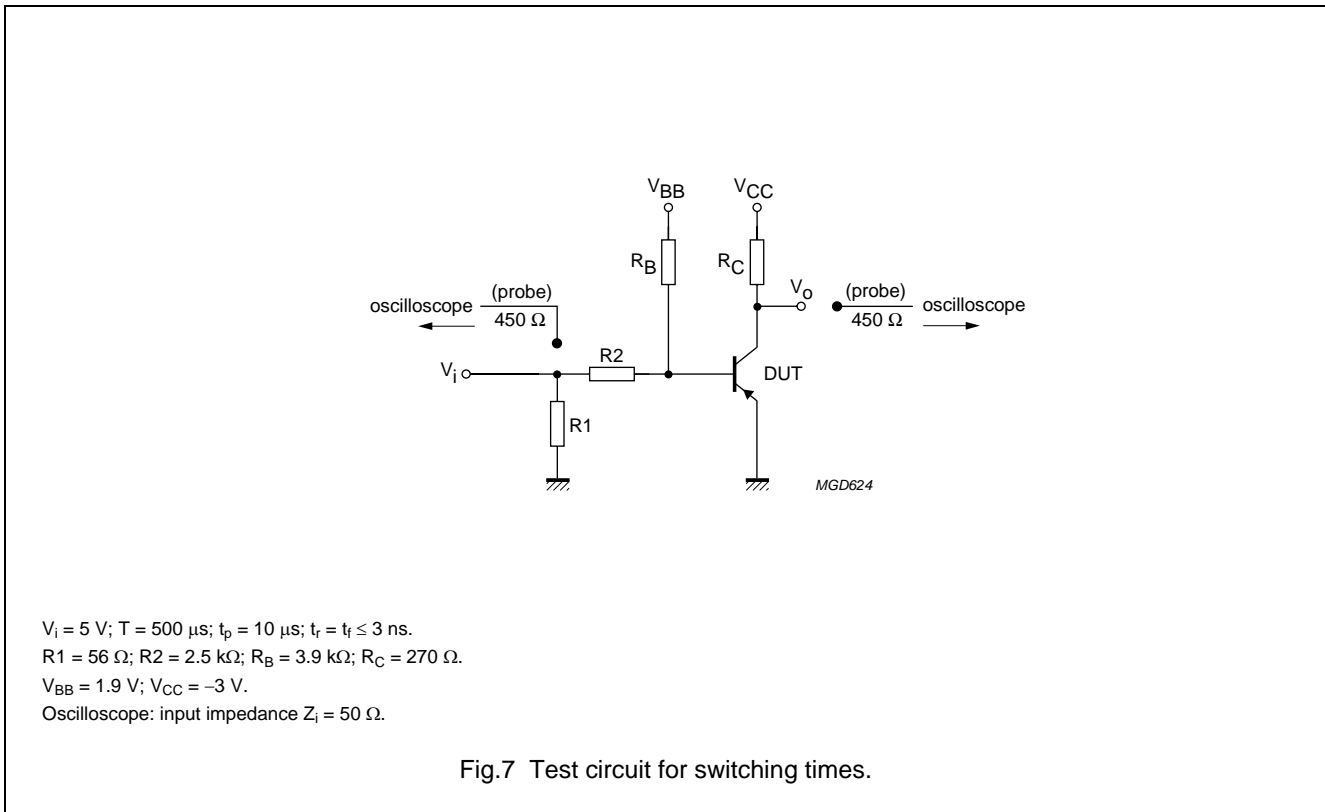
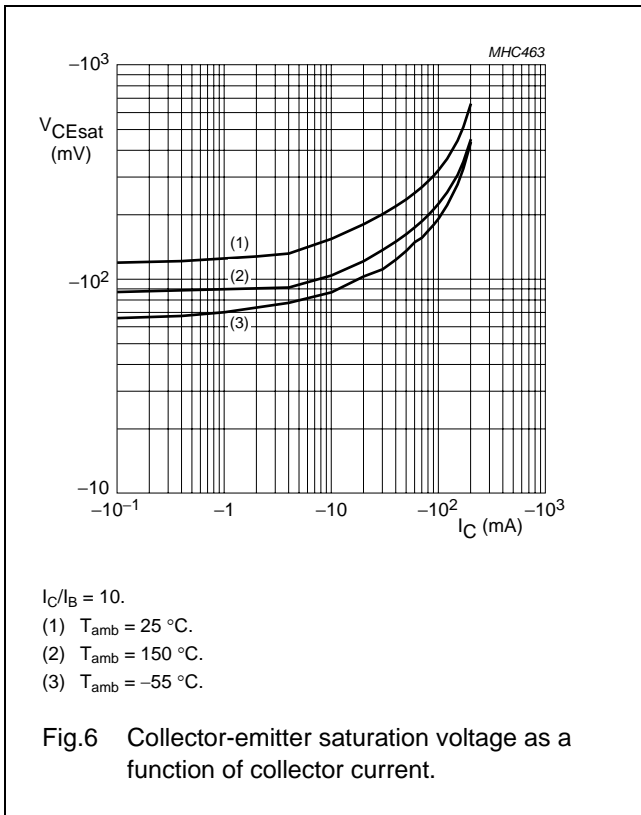
PNP switching transistor

MMBT3906



PNP switching transistor

MMBT3906



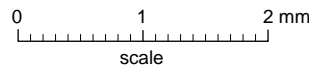
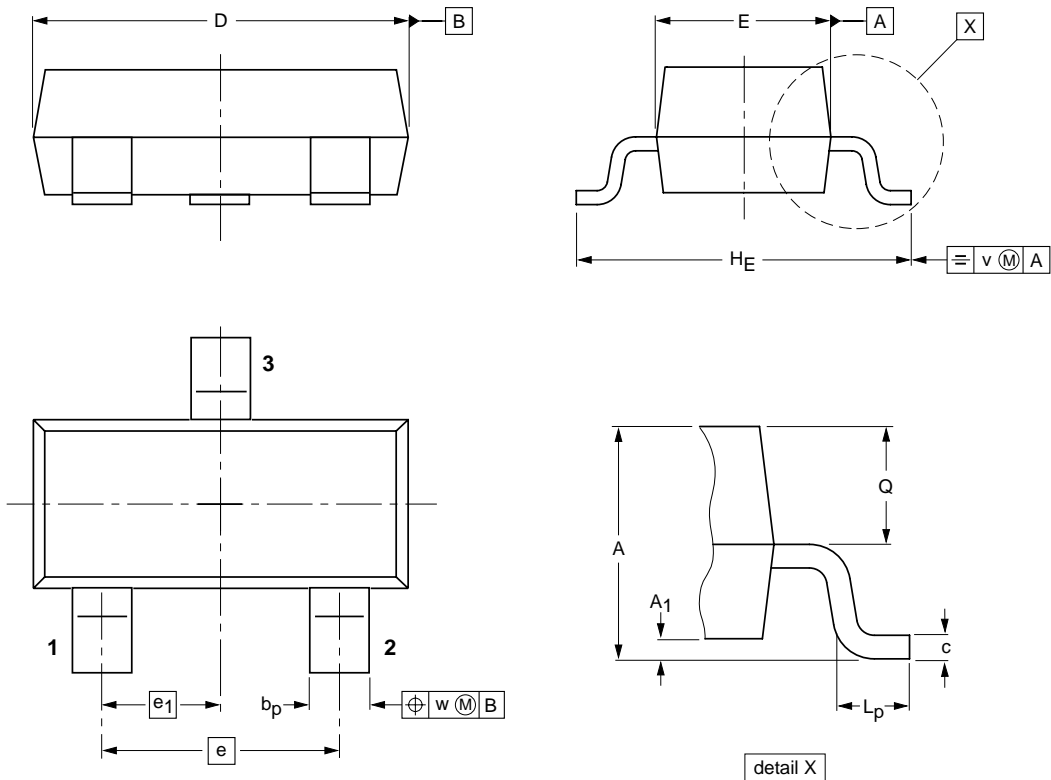
PNP switching transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				<del>97-02-28</del> 99-09-13

PNP switching transistor

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**DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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